



**REPLY UNDER 37 CFR §1.116**  
**EXPEDITED PROCEDURE**  
**TECHNOLOGY CENTER 1700**

**THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**Corres. and Mail**

**BOX AF**

In re application of:  
Vincent S. CHANG, et al.

Serial No.: 10/758,317

Filed: January 15, 2004

For: HIGH TEMPERATURE HYDROGEN  
ANNEALING OF A GATE INSULATOR  
TO INCREASE ETCHING SELECTIVITY  
BETWEEN CONDUCTIVE GATE  
STRUCTURE AND GATE INSULATOR  
LAYER

Group Art Unit: 1765

Examiner: Duy Vu Nguyen Deo

**Mail Stop AF**  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**AMENDMENT AFTER FINAL**

Sir:

In response to the Final Office Action mailed February 15, 2006, please amend the above-identified application as follows:

**Amendments to the Claims** are reflected in the listing of claims which begins on **page 2** of this paper.

**Remarks** begin on **page 8** of this paper.